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44. (Once Amended) A pair of adjacent capacitors fabricated relative to a semiconductor substrate, the adjacent capacitors having a minimum lateral spacing from one another which is less than the minimum [capable] photolithographic feature dimension [at the time of fabrication] with which the capacitors are fabricated.

45. (Once Amended) The capacitors of claim 44 wherein each comprises:
a stem; and
in cross-section, at least two laterally opposed fins interconnected with and projecting laterally from the stem, the stem having a minimum width which is less than the minimum [capable] photolithographic feature dimension [at the time of fabrication] with which the capacitors are fabricated.

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1 New Claims.

2 46. The capacitor construction of claim 43 wherein the stem
3 further comprises a maximum width which is less than the minimum
4 photolithographic feature dimension with which the capacitor is
5 fabricated.

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7 47. A capacitor construction comprising:

8 a stem; and

9 a plurality of elevationally spaced and laterally extending fins
10 interconnected with the stem, the individual fins having upper surfaces
11 which are planar across an entirety of the fins, the upper surfaces of
12 at least two of the fins being parallel to one another.

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14 48. The capacitor of claim 47 wherein the upper surfaces of all
15 of the fins are parallel to one another.

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17 49. The capacitor of claim 47 wherein the stem comprises a
18 minimum width which is less than the minimum photolithographic feature
19 dimension with which the capacitor is fabricated.
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Concluded
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50. The capacitor of claim 47 wherein the stem comprises a maximum width which is less than the minimum photolithographic feature dimension with which the capacitor is fabricated.

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